

# Are Heptazine-Based Organic Light-Emitting Diode (OLED) Chromophores

## Thermally Activated Delayed Fluorescence (TADF) or Inverted Singlet-Triplet (IST) Systems?

Andrzej L. Sobolewski<sup>1</sup> and Wolfgang Domcke<sup>2</sup>

<sup>1</sup> Institute of Physics, Polish Academy of Sciences, Warsaw, Poland

<sup>2</sup> Department of Chemistry, Technical University of Munich, Garching, Germany

### Supporting Information

Table S1. Vertical excitation energies ( $\Delta E$ ) and oscillator strengths ( $f$ ) of the lowest excited states of HAP-3MF, determined with the TDDFT/B3LYP/cc-pVDZ method at the DFT-D3/B3LYP/cc-pVDZ equilibrium geometry of the electronic ground state.

state	$\Delta E/\text{eV}$	$f$
$^3A'(\pi\pi^*)$	2.64	-
$^1A'(\pi\pi^*)$	2.81	0.0
$^3E'(\pi\pi^*)$	2.94	-
$^3A''(\text{n}\pi^*)$	3.45	-
$^1E'(\pi\pi^*)$	3.52	0.880
$^3E''(\text{n}\pi^*)$	3.54	-
$^1A''(\text{n}\pi^*)$	3.55	0.0
$^1E''(\text{n}\pi^*)$	3.65	0.0

Table S2. Vertical excitation energies ( $\Delta E$ ) and oscillator strengths ( $f$ ) of the lowest excited states of HAP-3TPA and truncated HAP-3TPA (HAP-3TPA-t), determined with the TDDFT/B3LYP/cc-pVDZ method at the DFT-D3/B3LYP/cc-pVDZ equilibrium geometry of the electronic ground state.

state	HAP-3TPA		HAP-3TPA-t	
	$\Delta E/\text{eV}$	$f$	$\Delta E/\text{eV}$	$f$
$^3E(\pi\pi^*)$	2.15	-	2.22	-
$^3A_1(\pi\pi^*)$	2.20	-	2.27	-
$^1E(\pi\pi^*)$	2.43	1.607	2.52	1.530
$^3A_2(\pi\pi^*)$	2.65	-	2.65	-
$^1A_1(\pi\pi^*)$	2.65	0.0	2.74	0.0
$^1A_2(\pi\pi^*)$	2.81	0.0	2.81	0.0

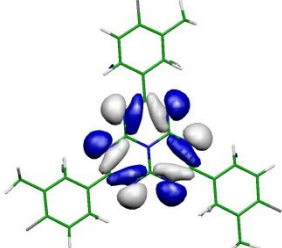
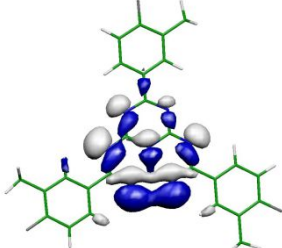
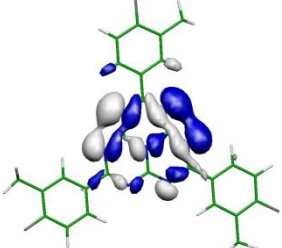
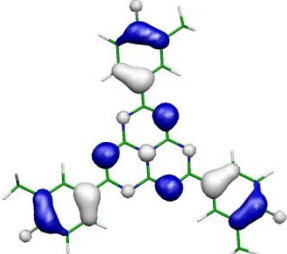
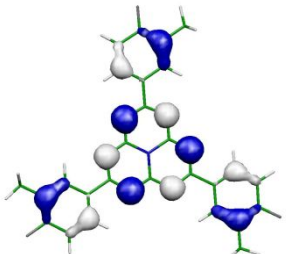
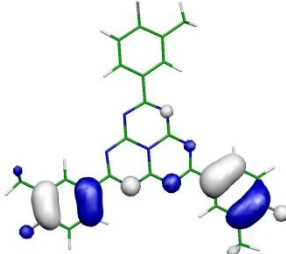
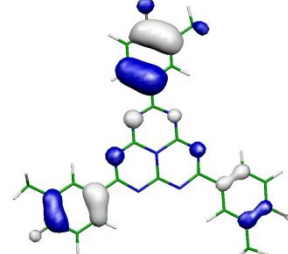
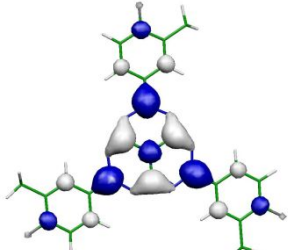
occupied orbitals			
104a' (-11.95)	105a' (-11.91)		106a' (-11.91)
			
19a'' (-9.38)	20a'' (-9.17)	21a'' (-9.16)	22a'' (-9.16)
			
LUMO			
23a'' (0.54)			
			

Figure S1. The highest occupied and lowest unoccupied Hartree-Fock orbitals involved in the lowest electronic excitations of HAP-3MF at the ground-state equilibrium geometry. The orbital energies (in eV) are shown in parentheses. Orbitals were plotted with an isosurface value of 0.03.

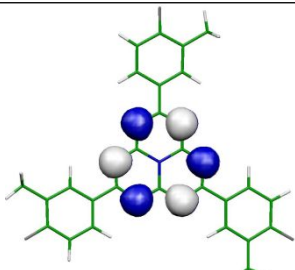
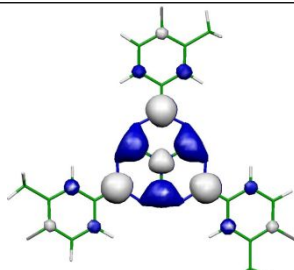
state	occ no.	hole	electron
$^1A'$	0.951		
$^3A'$	0.960		

Figure S2. Occupation numbers and natural transition orbitals involved in the excitation to the  $^1A'$  and  $^3A'$  excited states of HAP-3MF at the ground-state equilibrium geometry. Orbitals were plotted with an isosurface value of 0.03.

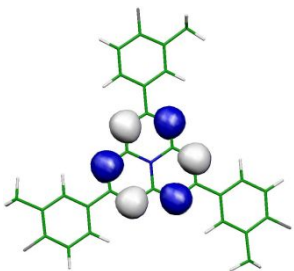
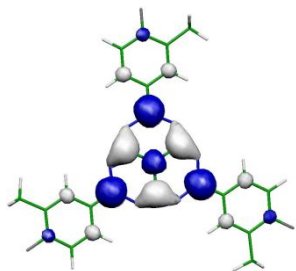
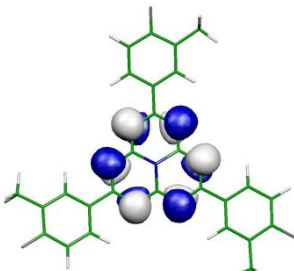
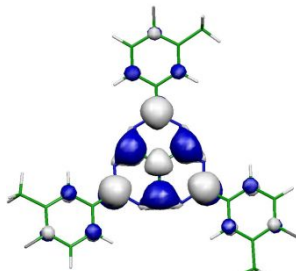
state	E <sub>ad</sub> /eV	E <sub>em</sub> /eV	occ. no.	hole	electron
C <sub>3h</sub> symmetry					
<sup>1</sup> A'	2.47	2.42	0.951		
<sup>3</sup> A'	2.72	2.67	0.974		
Δ <sub>ST</sub>	-0.25	-0.25			
C <sub>3</sub> symmetry					
S <sub>1</sub>	2.43	2.06	0.955		
T <sub>1</sub>	2.69	2.36	0.957		
Δ <sub>ST</sub>	-0.26	-0.30			

Figure S3. Adiabatic excitation energies ( $E_{ad}$ ), vertical emission energies ( $E_{em}$ ), natural occupation numbers, and natural transition orbitals of the lowest excited states of HAP-3MF, determined with the ADC(2)/cc-pVDZ method with the indicated symmetry constraints. Orbitals were plotted with an isosurface value of 0.03.

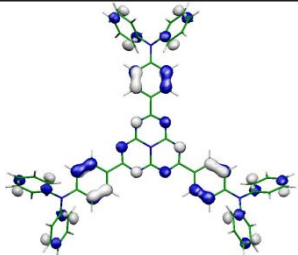
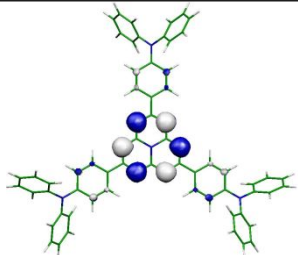
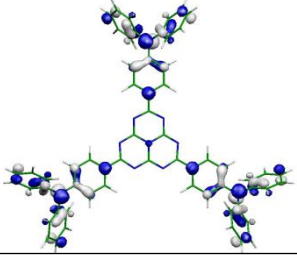
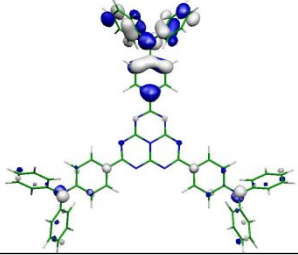
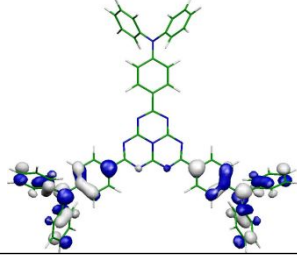
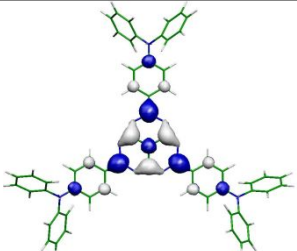
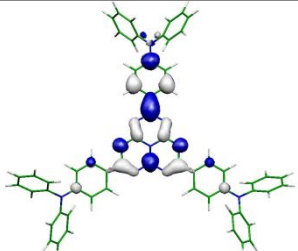
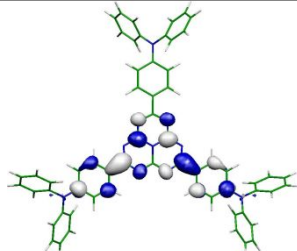
occupied orbitals		
117a (-9.13)	120a (-8.79)	
		
114b (-7.32)	115b (-7.24)	121a (-7.24)
		
unoccupied orbitals		
116b (0.93)	117b (1.80)	122a (1.80)
		

Figure S4. The highest occupied and lowest unoccupied Hartree-Fock orbitals involved in the lowest electronic excitations of HAP-3TPA-t at the ground-state equilibrium geometry. The orbital energies (in eV) are shown in parentheses. Orbitals were plotted with an isosurface value of 0.03.

state	occ no.	hole	electron
$^1A_1$	0.949		
$^3A_1$	0.957		
$^1E_x$	0.831		
$^3E_x$	0.770		
$^1E_y$	0.827		
$^3E_y$	0.759		

Figure S5. Occupation numbers and natural transition orbitals involved in the excitation to the lowest excited electronic states of HAP-3TPA-t at the ground-state equilibrium geometry. Orbitals were plotted with an isosurface value of 0.03.

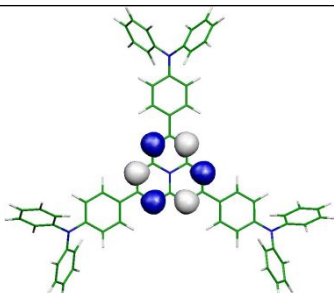
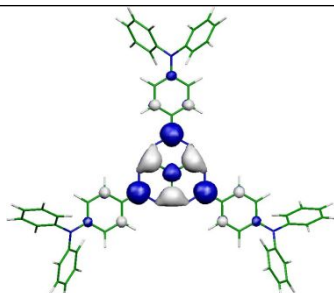
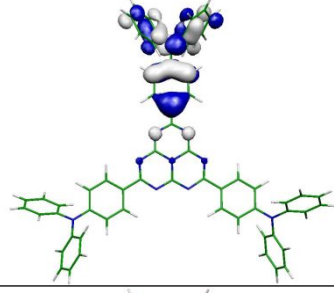
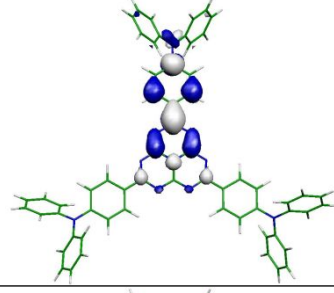
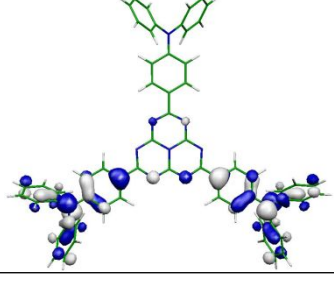
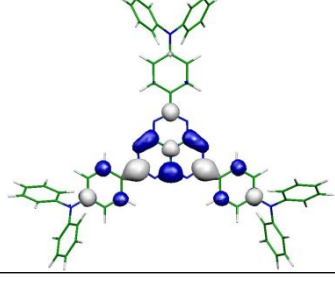
state	$E_{ad}/\text{eV}$	$E_{em}/\text{eV}$	occ. no.	hole	electron
$^1B$	2.50	2.42	0.950		
$^3E_x$	2.49	2.36	0.947		
$^3E_y$	2.55	2.48	0.768		

Figure S6. Adiabatic excitation energies ( $E_{ad}$ ) vertical emission energies ( $E_{em}$ ), natural occupation numbers, and natural transition orbitals of the lowest excited states of HAP-3TPA-t determined with the ADC(2)/def-SV(P) method at the equilibrium geometry of a given excited state. Orbitals were plotted with an isosurface value of 0.03.